

FEATURES
Complete RF Detector Function
Typical Range : –45 dBm to 0 dBm re 50 Ω
Frequency Response from 100 MHz to 2.7 GHz
Temperature-Stable Linear-in-dB Response
Accurate to 2.7 GHz
Rapid Response: 70 ns to a 10 dB Step
Low Power: 12 mW at 2.7 V
APPLICATIONS
Cellular Handsets (GSM, CDMA, WCDMA)
RSSI and TSSI for Wireless Terminal Devices
Transmitter Power Measurement
PRODUCT DESCRIPTION

The AD8312 is a complete low cost subsystem for the measurement of RF signals in the frequency range of 100 MHz to 2.7 GHz, with a typical dynamic range of 45 dB, intended for use in a wide variety of cellular handsets and other wireless devices. It provides a wider dynamic range and better accuracy than possible using discrete diode detectors. In particular, its temperature stability is excellent over the full operating range of –40°C to +85°C.

Its high sensitivity allows measurement at low power levels, thus reducing the amount of power that needs to be coupled to the detector. It is essentially a voltage-responding device, with a typical signal range of 1.25 mV to 224 mV rms or –45 dBm to 0 dBm re 50 Ω.

For convenience, the signal is internally ac-coupled, using a 5 pF capacitor to a load of 3 kΩ in shunt with 2 pF. This high-pass coupling, with a corner at approximately 16 MHz, determines the lowest operating frequency. Thus, the source may be dc-grounded.

The AD8312 output, called VOUT, increases from close to ground to about 1.2 V as the input signal level increases from 1.25 mV to 224 mV. This output is intended for use in measurement mode. Consult the Applications section of this data sheet for information on use in this mode. A capacitor may be connected between the VOUT and CFLT pins when it is desirable to increase the time interval over which averaging of the input waveform occurs.

The AD8312 is available in a 6-lead wafer-level chip scale package, 1.0 mm x 1.5 mm, and consumes 4.5 mA from a 2.7 V to 5.5 V supply.

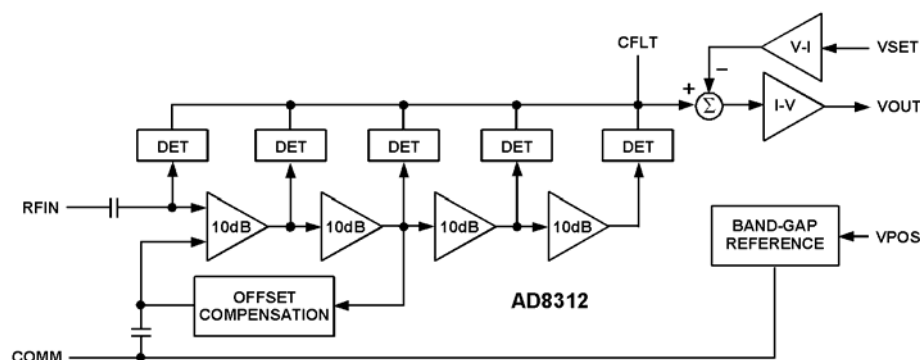
FUNCTIONAL BLOCK DIAGRAM


Figure 1.

PrA

10/29/2004

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.

One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106, U.S.A.
Tel: 781.329.4700 www.analog.com
Fax: 781.326.8703 © 2004 Analog Devices, Inc. All rights reserved.

TABLE OF CONTENTS

Specifications.....	3	Applications.....	11
Absolute Maximum Ratings.....	5	Basic Connections.....	11
ESD Caution.....	5	Evaluation Board.....	11
Pin Configuration and Function Descriptions.....	6	Outline Dimensions	13
Typical Performance Characteristics	7	Ordering Guide	13
General Description	10		

SPECIFICATIONS

Table 1. $V_S = 3\text{ V}$, $C_{FLT} = \text{open}$, $T_A = 25^\circ\text{C}$, $52.3\ \Omega$ termination resistor at RFIN, unless otherwise noted.

Parameter	Conditions	Min	Typ	Max	Unit
SIGNAL INPUT INTERFACE					
Specified Frequency Range	RFIN (Pin 6)	0.1		2.7	GHz
Input Voltage Range	Internally AC-Coupled	1.25		224	mV rms
Equivalent Power Range	52.3 Ω External Termination	-45		0	dBm
DC Resistance to COMM			100		k Ω
MEASUREMENT MODE					
VOUT (Pin 2) shorted to VSET (Pin 3), Sinusoidal Input Signal					
f = 0.1 GHz					
Input Impedance			3020 1.35		Ω pF
± 1 dB Dynamic Range	$T_A = +25^\circ\text{C}$		48		dB
	$-40^\circ\text{C} < T_A < +85^\circ\text{C}$		40		dB
Maximum Input Level	± 1 dB Error		2		dBm
Minimum Input Level	± 1 dB Error		-46		dBm
Slope			21.0		mV/dB
Intercept			-50.4		dBm
Output Voltage - High Power In	$P_{IN} = -10$ dBm		0.85		V
Output Voltage - Low Power In	$P_{IN} = -40$ dBm		0.22		V
Temperature Sensitivity	$P_{IN} = -10$ dBm				
	$25^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		-0.0002		dB/ $^\circ\text{C}$
	$-40^\circ\text{C} \leq T_A \leq +25^\circ\text{C}$		-0.0050		dB/ $^\circ\text{C}$
f = 0.9 GHz					
Input Impedance			903 1.16		Ω pF
± 1 dB Dynamic Range	$T_A = +25^\circ\text{C}$		50		dB
	$-40^\circ\text{C} < T_A < +85^\circ\text{C}$		40		dB
Maximum Input Level	± 1 dB Error		2		dBm
Minimum Input Level	± 1 dB Error		-48		dBm
Slope			20.3		mV/dB
Intercept			-51.4		dBm
Output Voltage - High Power In	$P_{IN} = -10$ dBm		0.839		V
Output Voltage - Low Power In	$P_{IN} = -40$ dBm		0.226		V
Temperature Sensitivity	$P_{IN} = -10$ dBm				
	$25^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		-0.0036		dB/ $^\circ\text{C}$
	$-40^\circ\text{C} \leq T_A \leq +25^\circ\text{C}$		-0.0010		dB/ $^\circ\text{C}$
f = 1.9 GHz					
Input Impedance			440 1.14		Ω pF
± 1 dB Dynamic Range	$T_A = +25^\circ\text{C}$		46		dB
	$-40^\circ\text{C} < T_A < +85^\circ\text{C}$		38		dB
Maximum Input Level	± 1 dB Error		-3		dBm
Minimum Input Level	± 1 dB Error		-49		dBm
Slope			19.4		mV/dB
Intercept			-51.8		dBm
Output Voltage - High Power In	$P_{IN} = -10$ dBm		0.815		V
Output Voltage - Low Power In	$P_{IN} = -40$ dBm		0.229		V
Temperature Sensitivity	$P_{IN} = -10$ dBm				
	$25^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		-0.0044		dB/ $^\circ\text{C}$
	$-40^\circ\text{C} \leq T_A \leq +25^\circ\text{C}$		-0.0027		dB/ $^\circ\text{C}$

Parameter	Conditions	Min	Typ	Max	Unit
f = 2.5 GHz					
Input Impedance			365 1.1		Ω pF
± 1 dB Dynamic Range	$T_A = +25^\circ\text{C}$ $-40^\circ\text{C} < T_A < +85^\circ\text{C}$		44		dB
Maximum Input Level	± 1 dB Error		36		dB
Minimum Input Level	± 1 dB Error		-4		dBm
Slope			-48		dBm
Intercept			18.85		mV/dB
Output Voltage - High Power In	$P_{IN} = -10$ dBm		-51		dBm
Output Voltage - Low Power In	$P_{IN} = -40$ dBm		0.774		V
Temperature Sensitivity	$P_{IN} = -10$ dBm $25^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +25^\circ\text{C}$		0.205		V
			+0.0053		dB/°C
			-0.0047		dB/°C
OUTPUT INTERFACE	VOUT (Pin 2)				
Minimum Output Voltage	No Signal at RFIN, $R_L \geq 10$ k Ω		0.02		V
Maximum Output Voltage ¹	$R_L \geq 10$ k Ω		2.2		V
General Limit	$2.7\text{ V} \leq V_S \leq 5.5\text{ V}$		$V_S - 1$		V
Available Output Current	Sourcing/Sinking		2/1		mA
Residual RF (at 2f)	f = 0.1 GHz (Worst Condition)		100		μV
Output Noise	RF Input = 2.2 GHz, -10 dBm, $f_{NOISE} = 100$ kHz, CFLT open		tbd		$\mu\text{V}/\sqrt{\text{Hz}}$
Fall Time	Input Level = off to 0 dBm, 90% to 10%		120		ns
Rise Time	Input Level = 0 dBm to off, 10% to 90%		85		ns
VSET INTERFACE	VSET (Pin 3)				
Input Resistance			10		k Ω
Bias Current Source	RFIN = -10 dBm; VSET = 1.2V		tbd		μA
POWER INTERFACE	VPOS (Pin 1)				
Supply Voltage		2.7	3.0	5.5	V
Quiescent Current			4.2		mA
vs. Temperature	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		4.3		mA

¹ Increased output possible when using an attenuator between VOUT and VSET to raise the slope.

ABSOLUTE MAXIMUM RATINGS

Table 2.

Parameter	Value
Supply Voltage VPOS	5.5 V
VOUT, VSET	0 V, VPOS
Input Voltage	1.6 V rms
Equivalent Power	+17 dBm
Internal Power Dissipation	TBD mW
θ_{JA} (WLCSP)	TBD°C/W
Maximum Junction Temperature	125°C
Operating Temperature Range	-40°C to +85°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature Range (Soldering 60 sec)	260°C

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

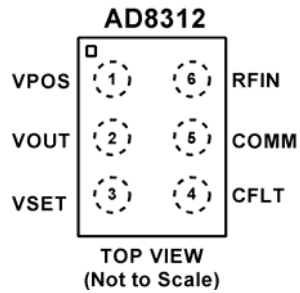


Figure 2. Pin Configuration

Table 3. Pin Function Descriptions

Pin	Mnemonic	Function
1	VPOS	Positive supply voltage (V_s), 2.7 V to 5.5 V.
2	VOUT	Logarithmic output. Output voltage increases with increasing input amplitude.
3	VSET	Setpoint input. Connect VSET to VOUT for measurement-mode operation.
4	CFLT	Connection for an external capacitor to slow the response of the output. Capacitor is connected between CFLT and VOUT.
5	COMM	Device Common (Ground)
6	RFIN	RF Input

TYPICAL PERFORMANCE CHARACTERISTICS

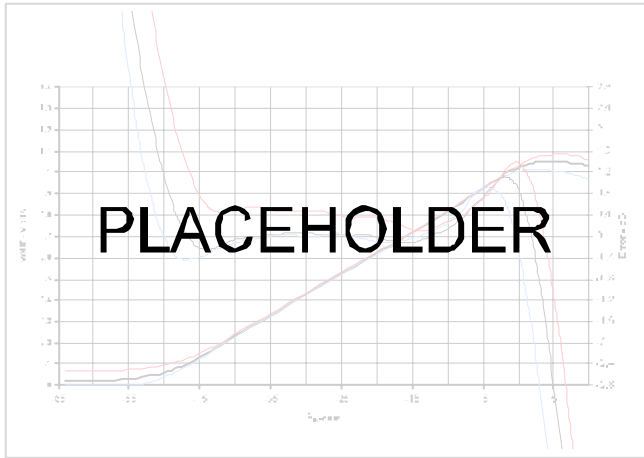


Figure 3. VOUT and Log Conformance vs. Input Amplitude at 50 MHz; -40°C, +25°C, and +85°C

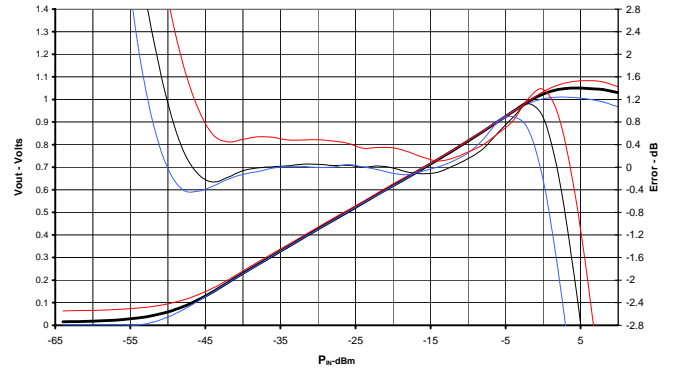


Figure 6. VOUT and Log Conformance vs. Input Amplitude at 1.9 GHz; -40°C, +25°C, and +85°C

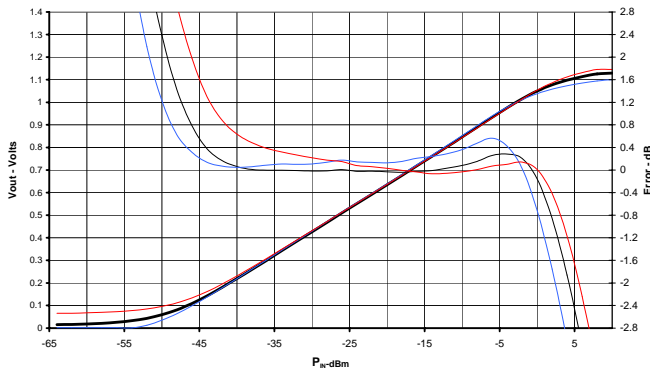


Figure 4. VOUT and Log Conformance vs. Input Amplitude at 100 MHz; -40°C, +25°C, and +85°C

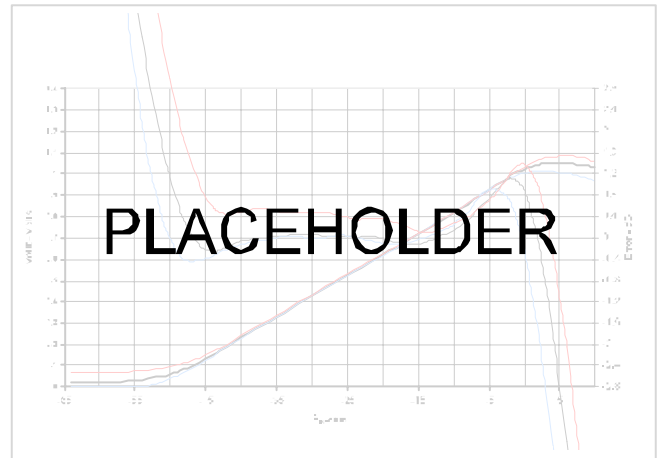


Figure 7. VOUT and Log Conformance vs. Input Amplitude at 2.2 GHz; -40°C, +25°C, and +85°C

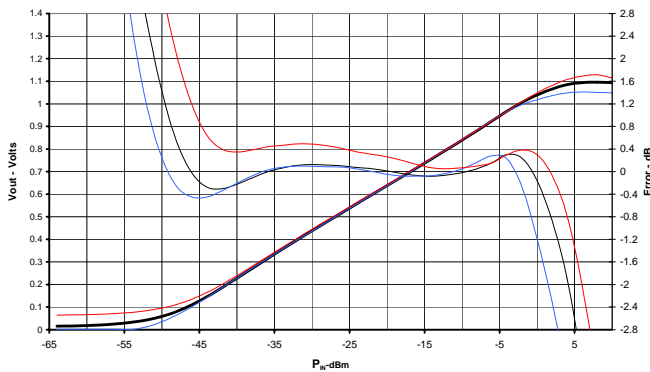


Figure 5. VOUT and Log Conformance vs. Input Amplitude at 900 MHz; -40°C, +25°C, and +85°C

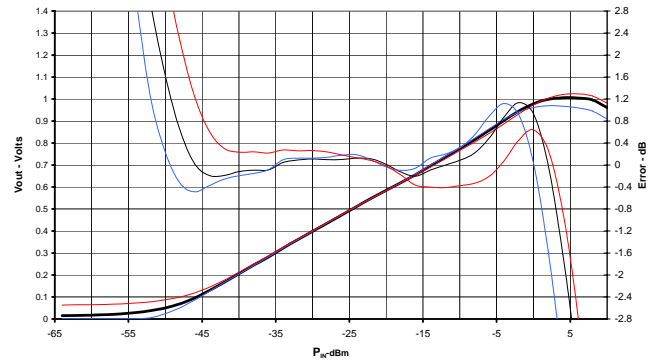


Figure 8. VOUT and Log Conformance vs. Input Amplitude at 2.5 GHz; -40°C, +25°C, and +85°C

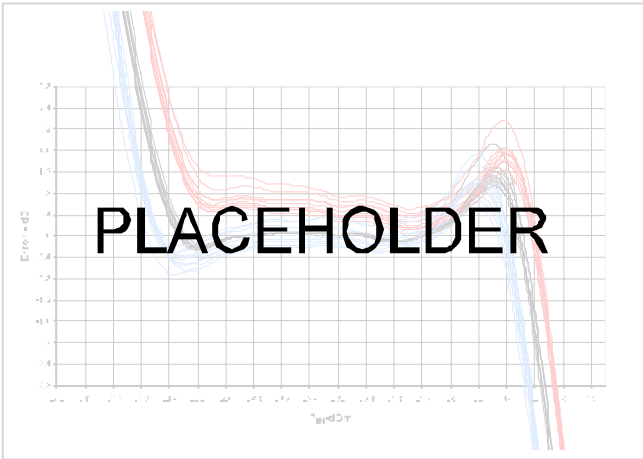


Figure 9. Distribution of Error over Temperature after Ambient Normalization vs. Input Amplitude at 50 MHz

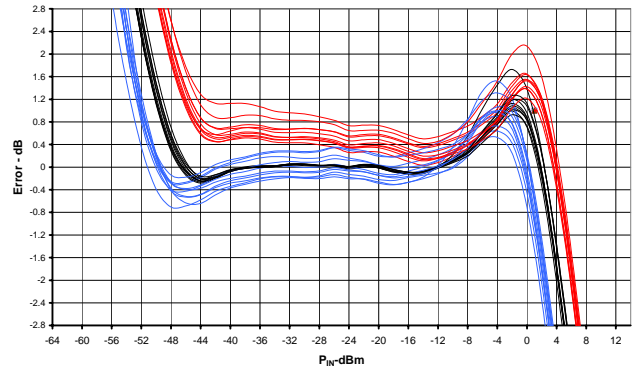


Figure 12. Distribution of Error over Temperature after Ambient Normalization vs. Input Amplitude at 1.9 GHz

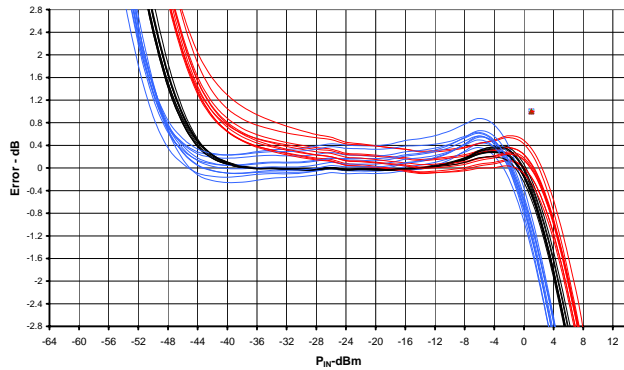


Figure 10. Distribution of Error over Temperature after Ambient Normalization vs. Input Amplitude at 100 MHz

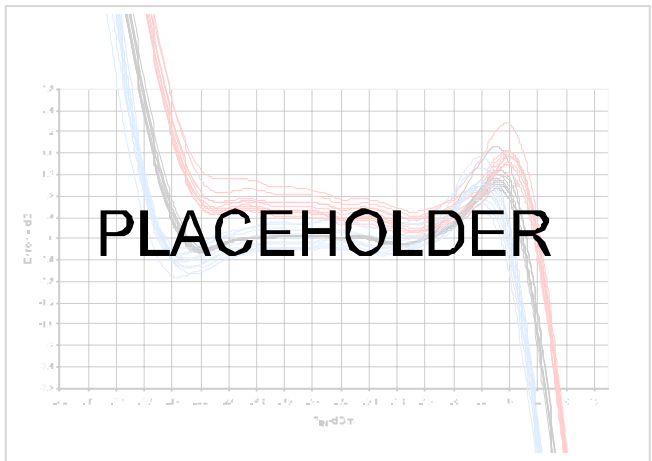


Figure 13. Distribution of Error over Temperature after Ambient Normalization vs. Input Amplitude at 2.2 GHz

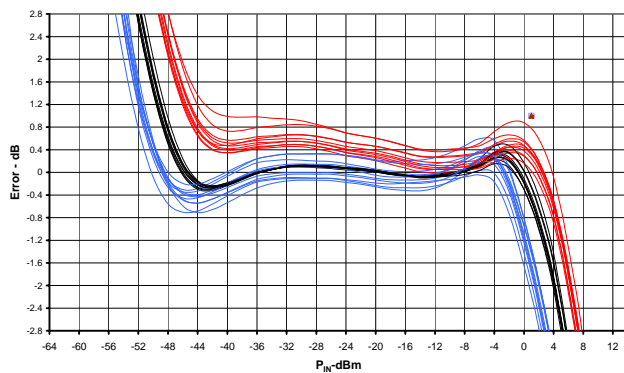


Figure 11. Distribution of Error over Temperature after Ambient Normalization vs. Input Amplitude at 900 MHz

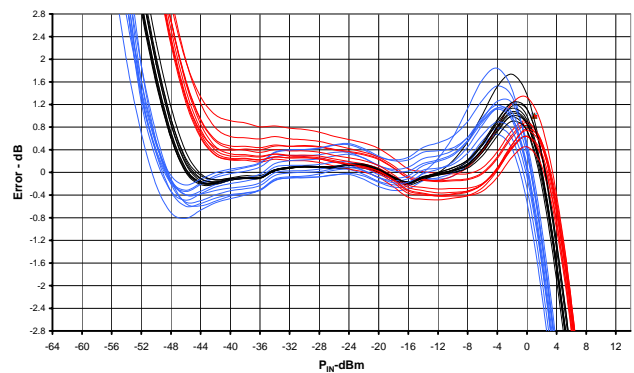


Figure 14. Distribution of Error over Temperature after Ambient Normalization vs. Input Amplitude at 2.5 GHz

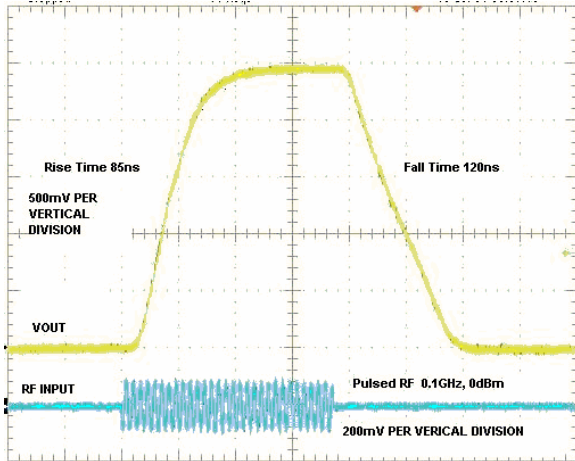


Figure 15. VOUT Response Time, RF Off to 0 dBm

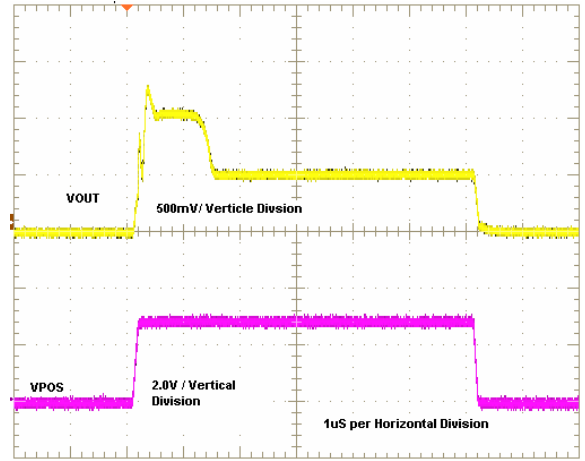


Figure 18. Power-On and Power-Off Response

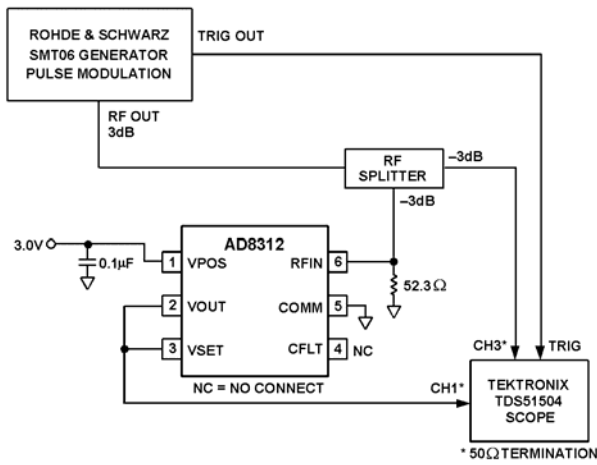


Figure 16. Test Setup for Pulse Response

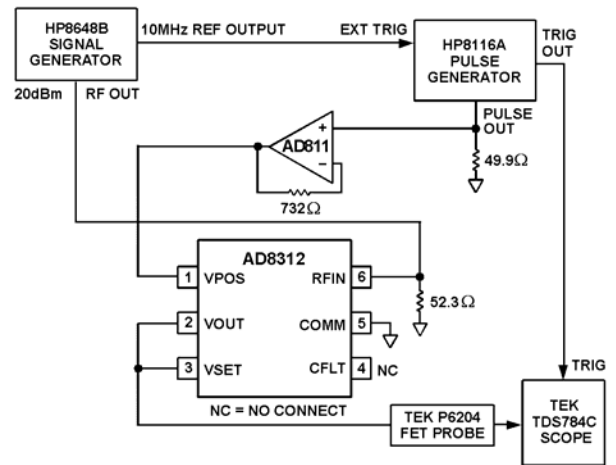


Figure 19. Test Setup for Power-On and Power-Off Response

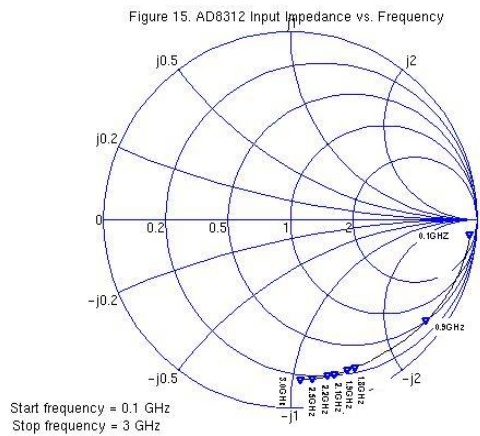


Figure 17. Input Impedance vs. Frequency; No Termination Resistor on RFIN

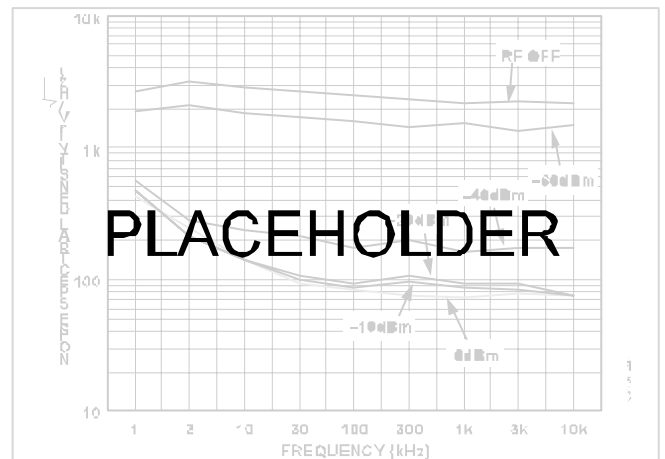


Figure 20. Noise Spectral Density of Output; C_{FLT} = Open

APPLICATIONS

BASIC CONNECTIONS

Figure 22 shows connections for the basic measurement mode. A supply voltage of 2.7 V to 5.5 V is required. The supply to the VPOS pin should be decoupled with a low inductance 0.1 μ F surface mount ceramic capacitor. A series resistor of about 10 Ω may be added; this resistor will slightly reduce the supply voltage to the AD8312 (maximum current into the VPOS pin is approximately 9 mA when VOUT is delivering 5 mA). Its use should be avoided in applications where the power supply voltage is very low (i.e., 2.7 V). A series inductor will provide similar power supply filtering with minimal drop in supply voltage.

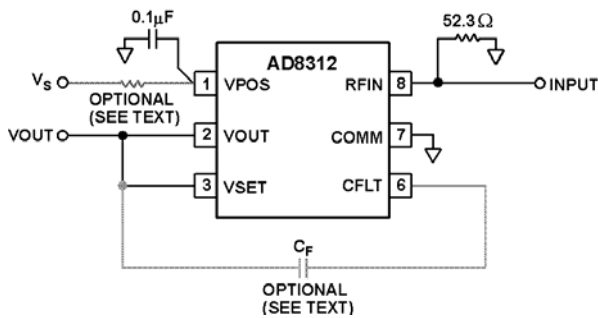


Figure 22. Basic Connections for Operation in Measurement Mode

The AD8312 has an internal input coupling capacitor. This eliminates the need for external ac-coupling. A broadband input match is achieved in this example by connecting a 52.3 Ω resistor between RFIN and ground. This resistance combines with the internal input impedance of approximately 3 k Ω to give an overall broadband input resistance of 50 Ω .

The measurement mode is selected by connecting VSET to VOUT, which establishes a feedback path and sets the logarithmic slope to its nominal value. The peak voltage range of the measurement extends from -45 dBm to 0 dBm at

0.9 GHz, and only slightly less at higher frequencies up to 2.5 GHz. At a slope of 21.5 mV/dB, this would amount to an output span of 967 mV. Figure 23 shows the transfer function for VOUT at a supply voltage of 3 V, and input frequency of 0.9 GHz.

The load resistance on VOUT should not be lower than 10 k Ω in order that the full-scale output of 1 V can be generated with the limited available current of 200 μ A max. Figure 23 shows the logarithmic conformance under the same conditions.

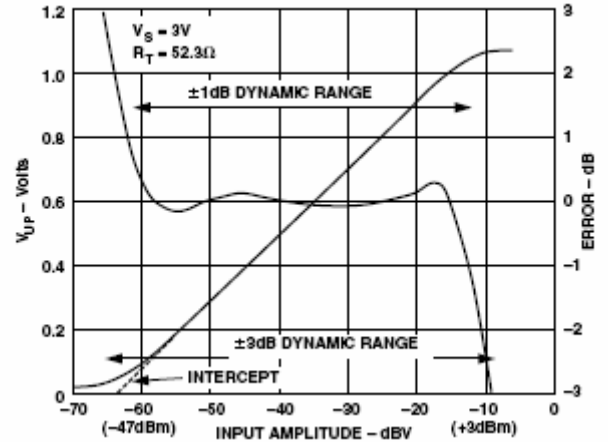


Figure 23. VOUT and Log Conformance Error vs. Input Level vs. Input Level

EVALUATION BOARD

Figure 24 shows the schematic of the AD8312 evaluation board. The layout and silkscreen of the component and circuit sides are shown in Figure 25 to Figure 28. The board is powered by a single supply in the range, 2.7 V to 5.5 V. The power supply is decoupled by a single 0.1 μ F capacitor.

Table 4 details the various configuration options of the evaluation board.

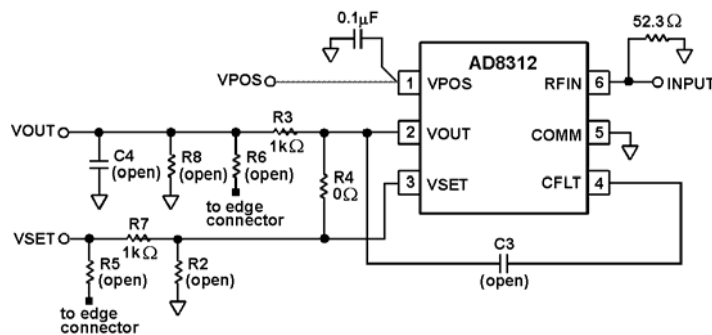


Figure 24. Evaluation Board Schematic

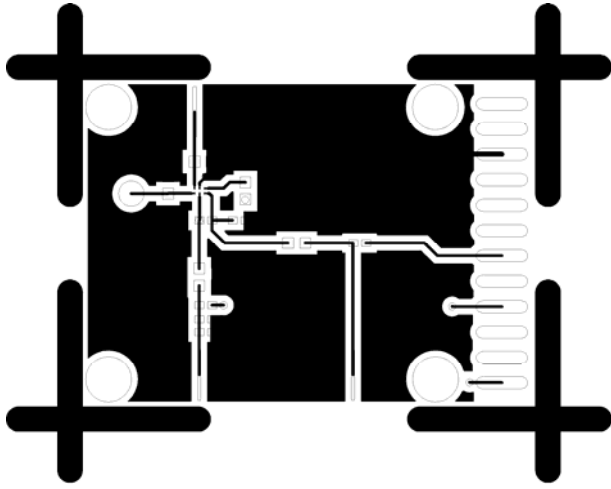


Figure 25. Layout of Component Side (WLCSP)

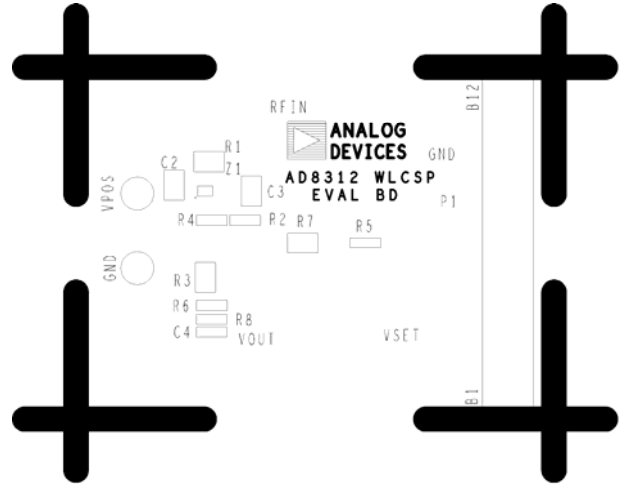


Figure 27. Silkscreen of Component Side (WLCSP)

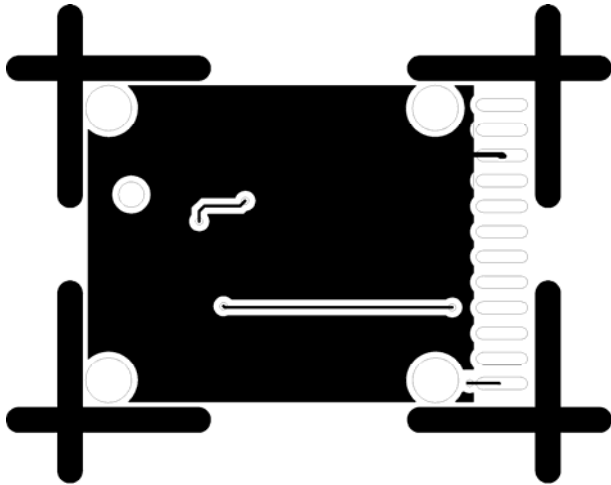


Figure 26. Layout of Circuit Side (WLCSP)

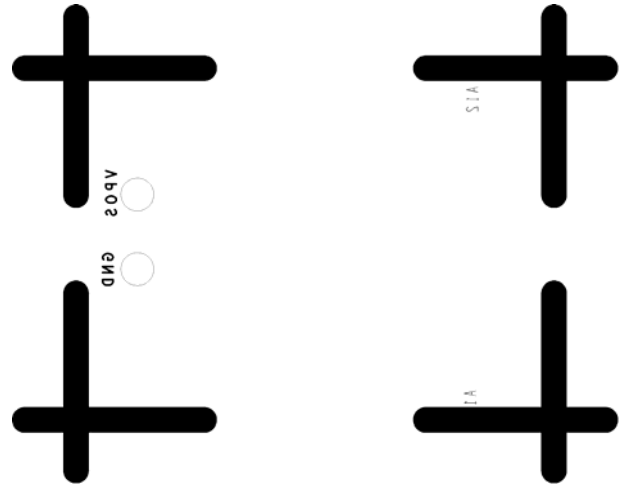


Figure 28. Silkscreen of Circuit Side (WLCSP)

Table 4. Evaluation Board Configuration Options

Component	Function	Default Condition
VPOS, GND	Supply and Ground Vector Pins	Not Applicable
C2	Power Supply Decoupling: The nominal supply decoupling consists of a 0.1 μF capacitor (C1).	C2 = 0.1 μF (Size 0603)
R1	Input Interface: The 52.3 Ω resistor in position R1 combines with the AD8312's internal input impedance to give a broadband input impedance of around 50 Ω .	R1 = 52.3 Ω (Size 0603)
R2, R4	Slope Adjust: By installing resistors in R2 and R4, the nominal slope of 20 mV/dB can be changed. See Slope Adjust discussion for more details.	R2 = Open (Size 0402) R4 = 0 Ω (Size 0402)
C3	Filter Capacitor. The response time of VOUT can be modified by placing a capacitor between CFLT (Pin 4) and VOUT.	C3 = Open (Size 0603)
R3, R8, C4	Output Interface: R3, R8, and C4 can be used to check the response of VOUT to capacitive and resistive loading. R3/R8 can be used to attenuate VOUT.	R3 = 1k Ω (Size 0603) R8 = C4 = open (Size 0402)
R7	VSET Interface: R7 can be used to reduce capacitive loading from transmission lines.	R7 = 1k Ω (Size 0603)
R5, R6	Alternate Interface: R5 and R6 allow for VOUT and VSET to be accessible from the edge connector	R5 = R6 = Open (Size 0402)

OUTLINE DIMENSIONS

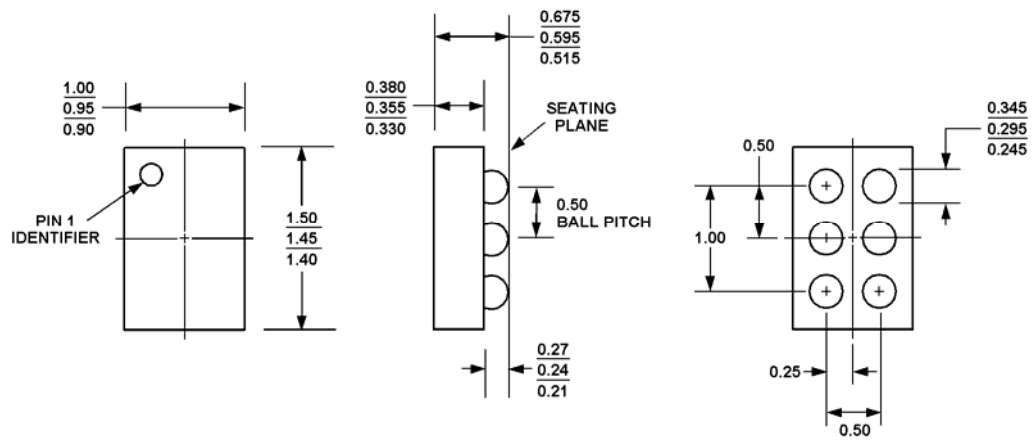


Figure 29. Wafer-level Chip Scale Package
Dimensions shown in mm

ORDERING GUIDE

AD8312 Products	Temperature Package	Package Description	Package Outline	Branding Information	Ordering Quantity
AD8312ACPZ-REEL7 ¹	-40°C to +85°C	6-Lead Wafer-level Chip Scale Package, 7" Tape and Reel	CB-6	Q00	tbd
AD8312ACPZ-WP AD8312-EVAL	-40°C to +85°C	6-Lead WLCSP, Waffle Pack Evaluation Board	CB-6	Q00	tbd

¹Z = Pb-free part.